IN THE CLAIMS

This listing of claims replaces all prior listings and versions of the claims in the present application.

Listing of Claims:

Claims 1-6 (Canceled).

Claim 7 (Currently Amended): A susceptor that is used in semiconductor epitaxial growth, comprising:

a barrel type susceptor having a plurality of surfaces on an outer side of each of which a plurality of substrates is freely disposed; and

a member that has the barrel type susceptor disposed ~~inside thereof~~ therein and which has surfaces each of which ~~is oppositely disposed tilting in a same direction and a same distance from the surfaces as each of the surfaces of the barrel type susceptor~~ are equally distanced from and are positioned parallel to the surfaces of said barrel type susceptor; and

wherein the barrel type susceptor and said member comprise a heater.

Claim 8 (Previously Presented): The susceptor according to claim 7, wherein each of surfaces on a side of the barrel type susceptor of the member allows placing a plurality of substrates.

Claim 9 (Previously Presented): The susceptor according to claim 7, wherein either one or both of the barrel type susceptor and the member are a heater.

Claim 10 (Previously Presented): The susceptor according to claim 7, wherein the susceptor is made of a base material containing graphite.

Claim 11 (Previously Presented): The susceptor according to claim 10, wherein the susceptor is covered with polycrystalline silicon carbide or polycrystalline tantalum carbide.

Claim 12 (Currently Amended): A susceptor that is used in semiconductor epitaxial growth, comprising:

a barrel type susceptor having a plurality of surfaces on an inner side of each of which a plurality of substrates is freely disposed; and

a member that has the barrel type susceptor disposed at [[the]] a peripheral portion thereof and which has surfaces ~~each of~~ which ~~is oppositely disposed tilting in a same direction and a same distance from the surfaces as each of the surfaces of the barrel type susceptor~~ are equally distanced from and are positioned parallel to the surfaces of said barrel type susceptor, respectively; and

wherein the barrel type susceptor and said member comprises a heater.

Claim 13 (Currently Amended): The susceptor according to claim 12, wherein each of said surfaces on a side of the barrel type susceptor of the member allows placing a plurality of substrates thereon.

Claim 14 (Currently Amended): The susceptor according to claim 12, wherein either one or both of the barrel type susceptor and the member [[are]] comprise a heater.

Claim 15 (Previously Presented): The susceptor according to claim 12, wherein the susceptor is made of a base material containing graphite.

Claim 16 (Previously Presented): The susceptor according to claim 15, wherein the susceptor is covered with polycrystalline silicon carbide or polycrystalline tantalum carbide.

Claim 17 (Previously Presented): The susceptor according to claim 7, wherein said barrel type susceptor is fixedly held in position within said member.

Claim 18 (Previously Presented): The susceptor according to claim 12, wherein said barrel type susceptor is fixedly held in position within said member.

Claim 19 (New): A susceptor according to claim 7, wherein during the semiconductor epitaxial growth, a distance between surfaces of the plurality of substrates disposed on the barrel type susceptor and surfaces of the member is maintained substantially equidistant from one another and said surfaces of the member are maintained parallel to the surfaces of the barrel type susceptor.

Claim 20 (New): An epitaxial growth unit, comprising:

the susceptor as claimed in claim 7 and which further comprises a heat insulating material is positioned outside the susceptor.

Claim 21 (New): A susceptor according to claim 12, wherein during the semiconductor epitaxial growth, a distance between surfaces of the plurality of substrates disposed on the barrel type susceptor and surfaces of the member is maintained substantially equidistant from one another and said surfaces of the member are maintained parallel to the surfaces of the barrel type susceptor.

Claim 22 (New): An epitaxial growth unit, comprising:

the susceptor according to claim 12; and further comprising a heat insulating material disposed outside the susceptor.